

What is claimed is:

1. A semiconductor laser, comprising:
 - a semiconductor laser cavity having at least one segment and at least one output;
 - at least one etched gap located in said at least one segment; and
 - at least one distributed Bragg reflector (DBR) at said at least one output.
2. The laser of claim 1, wherein the total length of said laser cavity is between about 10 μm and about 10,000 μm .
3. The laser of claim 1, wherein said at least one etched gap has a length of between about 0.001 μm and about 10 μm .
4. The laser of claim 1, further including at least one photonic device connected to said at least one output of said laser cavity.
5. The laser of claim 1, wherein the laser is a ring laser.
6. The laser of claim 1, wherein the laser is a V-shaped laser.
7. A semiconductor laser, comprising:
 - a semiconductor laser cavity having at least one segment and at least one output;
 - at least one etched gap located in at least one segment of the laser,
 - at least one photonic device connected to said at least one output of said laser, and
 - at least an etched facet at or near the Brewster angle at one end of said photonic device.
8. The laser of claim 7, wherein the total length of said laser cavity is between about 10 μm and about 10,000 μm .

9. The laser of claim 7, wherein said at least one etched gap has a length of between about 0.001 μm and about 10 μm .

10. A semiconductor photonic device, comprising:

a cavity having at least one segment; and
at least an etched facet at or near the Brewster angle at one end of said at least one segment.

11. The photonic device of claim 10, wherein said cavity includes an entrance facet and an exit facet.

12. The photonic device of claim 10, wherein said entrance facet is directly coupled to another photonic device.

13. The photonic device of claim 10, wherein said photonic device is a V-shaped structure and wherein said at least one segment includes a first and a second leg.

14. The photonic device of claim 13, wherein said etched facet at or near the Brewster angle is at an end of said first leg of said V-shaped structure.

15. The photonic device of claim 14, wherein said first and second legs are joined at corresponding ends to form said V-shaped structure, and wherein an exit facet is positioned at the joint of the said first and second legs.

16. The photonic device of claim 15, further including an entrance facet at a free end of said second leg of said V-shaped structure.